

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device, ~~comprising~~ ~~consisting~~ of structural elements in the following order:

a plastic substrate,

a layer fabricated with pulsed radiation, said layer fabricated with pulsed radiation positioned above said plastic substrate,

a layer that can be damaged by said pulsed radiation, said layer that can be damaged by said pulsed radiation positioned above said plastic substrate and operatively connected to said layer fabricated with pulsed radiation, and

a narrowband reflective coating layer, said narrowband reflective coating layer positioned above said layer that can be damaged by pulsed radiation, positioned above said plastic substrate, and operatively connected to said layer that can be damaged by said pulsed radiation, and

wherein said narrowband reflective coating layer is positioned over said layer that can be damaged by said pulsed radiation for reflecting said pulsed radiation and protecting said layer that can be damaged by said pulsed radiation.

2. (Original) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic.

3. (Previously Presented) The semiconductor device of claim 1 wherein said reflective coating layer is single layer or multiple layers for narrowband reflection.

4. (Previously Presented) The semiconductor device of claim 3 wherein said reflective coating layer is a narrow band reflectance coating.

5. (Currently Amended) The semiconductor device of claim 1 wherein said reflective coating layer comprises the materials ~~SiNx~~ Si<sub>3</sub>N<sub>4</sub> and SiO<sub>2</sub>.

6. (Previously Presented) The semiconductor device of claim 1 wherein said reflective coating layer comprises the materials HfOx and SiO<sub>2</sub>.

7. (Currently Amended) The semiconductor device of claim 1 wherein said reflective coating layer comprises the materials ~~SiNx~~ Si<sub>3</sub>N<sub>4</sub> and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm.

8. (Previously Presented) The semiconductor device of claim 1 wherein said reflective coating layer comprises the materials HfOx and SiO<sub>2</sub> that will give greater than 99% reflection at 308nm..

9. (Previously Presented) The semiconductor device of claim 1 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation and operatively connected to said narrowband reflective coating layer for reflecting said pulsed radiation.

10. (Previously Presented) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic, said reflective coating layer is single layer or multiple layers for narrowband reflection, and said layer fabricated with pulsed radiation is a layer that has been fabricated with high intensity radiation sources.

11. (Previously Presented) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is polyester.

12. (Currently Amended) The semiconductor device of claim 1 wherein said reflective coating layer is a narrow band reflectance coating comprising the materials ~~SiNx Si<sub>3</sub>N<sub>4</sub>~~ and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm.

13. (Currently Amended) The semiconductor device of claim 1 including an insulating layer operatively connected to said layer that can be damaged by said pulsed radiation and wherein said reflective coating layer is a narrow band reflectance coating comprising the materials ~~SiNx Si<sub>3</sub>N<sub>4</sub>~~ and SiO<sub>2</sub> that has a high reflectance in the UV, greater than 70% for wavelengths between 300nm and 335nm for reflecting said pulsed radiation.